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600V, 40A, Trench FS II Fast IGBT

General Description:

Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FSIIIGBT offers superior conduction and switching performances, and easy parallel operation;

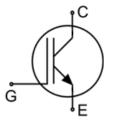
Features

Trench FSII Technology offering

- Very low V_{CE (sat)}
- High speed switching
- Positive temperature coefficient in V_{CE} (sat)
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Air Condition
- Inverters
- Motor drives



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE40T60BP	TO-3PNT	NCE40T60BP



TO-3PNT

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
Vces	Collector-Emitter Voltage	600	V
V _{GES}	Gate- Emitter Voltage	±30	V
Ic	Collector Current	80	А
IC	Collector Current @T _C = 100 °C	40	Α
I _{Cplus}	Pulsed Collector Current, tp limited by Tjmax	120	А
-	turn off safe operating area, VcE=600V, Tj=150°C	120	А
P _D	Power Dissipation @ T _C = 25°C	286	W
PD	Power Dissipation @T _C = 100 °C	114	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
TL	Maximum Temperature for Soldering	260	°C
t _{sc}	Short circuit withstand time V_{GE} =15V, V_{CC} \leq 400V, Allowed number of short circuits<1000Time between short circuits: \geq 1.0s, T_j \leq 150°C	3	us



NCE40T60BP

Thermal Characteristic

Symbol	Parameter	Value	Units
Rejc	Thermal Resistance, Junction to case for IGBT	0.43	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	°C/W

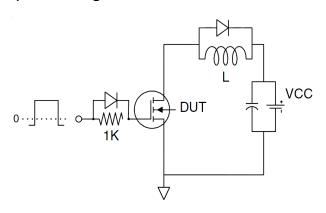
Electrical Characteristics (Tc=25°C unless otherwise noted)

0	Barranatan	T O . I''		Value			
Symbol	mbol Parameter Test Conditions		naitions	Min.	Тур.	Max.	Units
Static Chara	cteristics						
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V,I _{CE} =1mA		600			V
Ices	Collector-Emitter Leakage Current	V _{GE} =0V,V _{CE} =600V				4	uA
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30V,V _{CE} =0V				200	nA
I _{GES(R)}	Gate to Source Reverse Leakage	V _{GE} =-30	V,Vce =0V			200	nA
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =40A	Tj=25°C		1.7	1.9	V
		V _{GE} =15V	Tj=150°C		1.9		V
V _{GE(th)}	Gate Threshold Voltage	I _C =1mA,V _{CE} =V _{GE}		4.0	5.0	6.0	V
Dynamic Ch	aracteristics				1		
Cies	Input Capacitance	V _{CE} =25V,V _{GE} =0V, f=1MHz			4894		pF
Coes	Output Capacitance				136		
C_{res}	Reverse Transfer Capacitance				94		
Q_{g}	Total Gate Charge	Vcc=480V, Ic=40A V _{GE} =15V			176		nC
Q_{ge}	Gate to Emitter Charge				38		
Q_{gc}	Gate to Collector Charge				73		
I _{C(SC)}	Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s	V _{GE} =15V,V _{CC} ≤400V, t _{SC} ≤3us,Tj≤150°C			250		А
Switching Cl	haracteristics						
$t_{d(ON)}$	Turn-on Delay Time				19		
t _r	Rise Time	V_{CC} =400V,Ic=40A V_{GE} =0/15V, R_g =5 Ω Inductive Load			17		ns
$t_{\text{d(OFF)}}$	Turn-Off Delay Time				168		
t _f	Fall Time				16		
Eon	Turn-On Switching Loss				0.58		
E _{off}	Turn-Off Switching Loss				0.48		mJ
E _{ts}	Total Switching Loss				1.06		

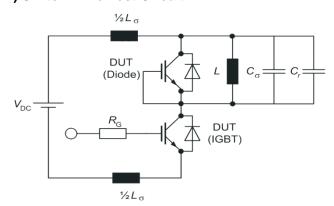


Test Circuit

1) Gate Charge Test Circuit

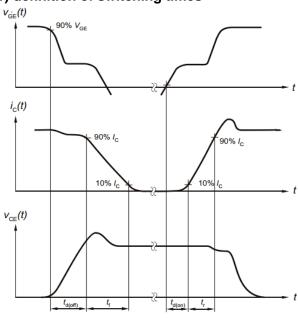


2) Switch Time Test Circuit

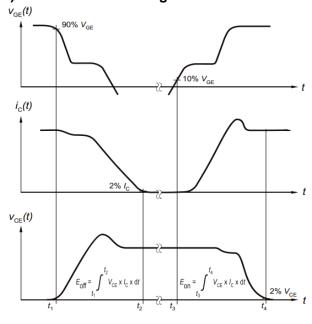


Switching characteristics

1) definition of switching times



2) definition of switching losses



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Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

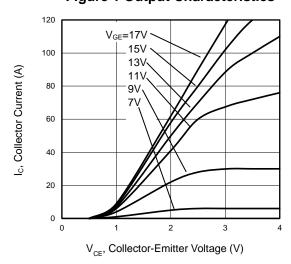


Figure 3 V_{CEsat} vs. Case Temperature

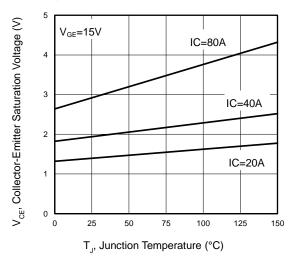


Figure 5 Capacitance Characteristics

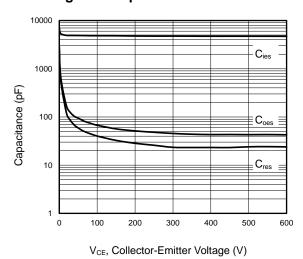


Figure 2 Transfer Characteristics

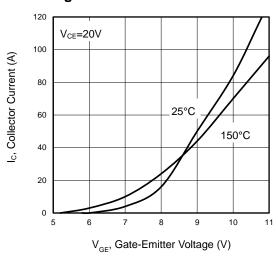


Figure 4 Saturation Voltage vs. V_{GE}

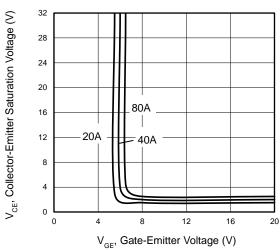
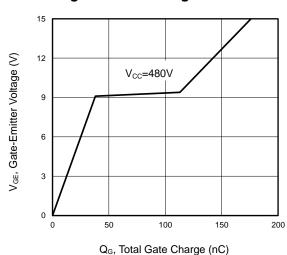


Figure 6 Gate charge waveform





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Typical Electrical and Thermal Characteristics

Figure 7 Typical Switching Times as a **Function of Gate Resistor**

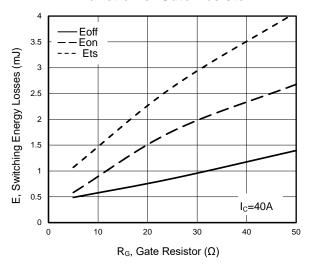


Figure 9 Gate-emitter Threshold Voltage as a **Function of Junction Temperature**

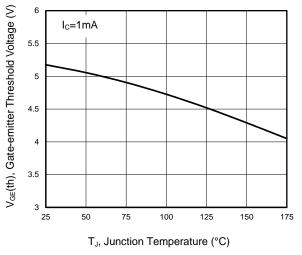
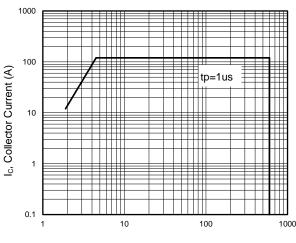
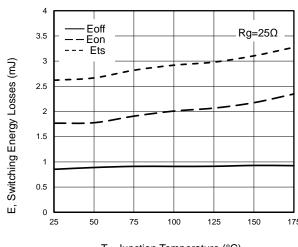


Figure 11 Forward Bias Safe Operating Area



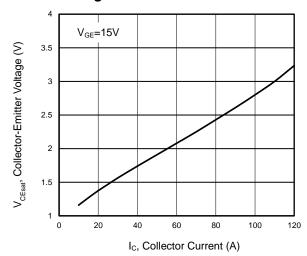
V_{CE}, Collector-Emitter Voltage (V)

Figure 8 Typical Switching Times as a **Function of Junction Temperature**



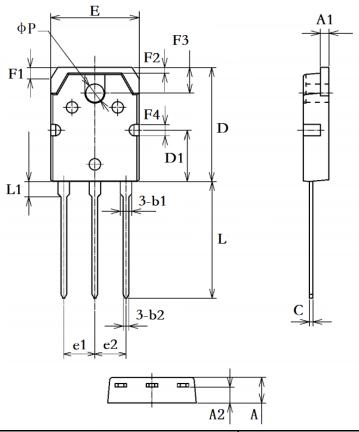
T_J, Junction Temperature (°C)

Figure 10 Typical Collector-emitter Saturation Voltage as a function of Collector Current





TO-3PNT Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
Cymbol	Min.	Max.	Min.	Max.	
А	4.35	4.65	0.17	0.18	
A1	1.40	1.60	0.06	0.06	
A2	2.60	3.00	0.10	0.12	
b1	1.90	2.30	0.07	0.09	
b2	0.90	1.10	0.04	0.04	
С	0.50	0.70	0.02	0.03	
D	19.70	20.30	0.78	0.80	
D1	7.30	7.90	0.29	0.31	
E	15.20	15.80	0.60	0.62	
e1/e2	5.35	5.55	0.21	0.22	
F1	1.50	2.50	0.06	0.10	
F2	0.70	1.30	0.03	0.05	
F3	4.60	4.90	0.18	0.19	
F4	2.10	2.50	0.08	0.10	
L	19.50	21.5	0.77	0.85	
L1	2.10	3.30	0.08	0.13	
ФР	3.00	3.40	0.12	0.13	



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